Standard Rectifier

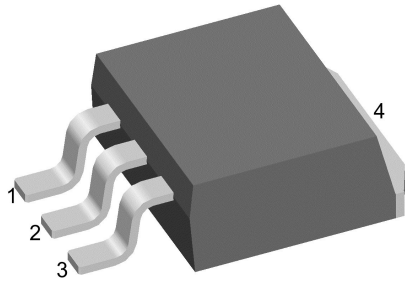
V_{RRM}	=	2x 1200 V
I_{FAV}	=	8 A
V_F	=	1.08 V

Phase leg

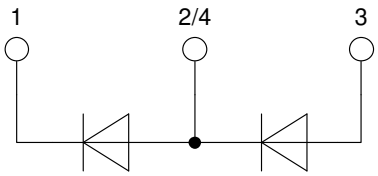
Part number

DSP8-12AS

Marking on Product: DSP8-12AS



Backside: anode/cathode



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very low forward voltage drop
- Improved thermal behaviour

Applications:

- Diode for main rectification
- For single and three phase bridge configurations

Package: TO-263 (D2Pak)

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

Disclaimer Notice

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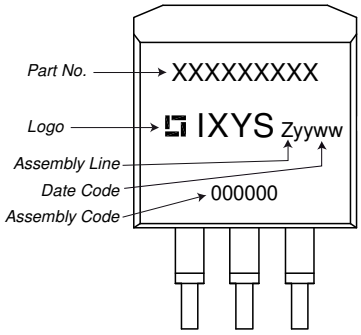
Rectifier

Symbol	Definition	Conditions		Ratings min.	typ.	max.	Unit
V_{RSM}	*max. non-repetitive reverse blocking voltage*		T_{VJ} = 25°C			1300	V
V_{RRM}	*max. repetitive reverse blocking voltage*		T_{VJ} = 25°C			1200	V
I_R	*reverse current*	V_R = 1200 V	T_{VJ} = 25°C			10	µA
		V_R = 1200 V	T_{VJ} = 150°C			0.2	mA
V_F	*forward voltage drop*	I_F = 8 A	T_{VJ} = 25°C			1.16	V
		I_F = 16 A				1.35	V
		I_F = 8 A	T_{VJ} = 150°C			1.08	V
		I_F = 16 A				1.34	V
I_{FAV}	*average forward current*	T_C = 160°C	T_{VJ} = 175°C			8	A
		rectangular d = 0.5					
V_{F0}	*threshold voltage* } *for power loss calculation only*		T_{VJ} = 175°C			0.79	V
r_F	*slope resistance* }					30	mΩ
R_{thJC}	*thermal resistance junction to case*					1.5	K/W
R_{thCH}	*thermal resistance case to heatsink*				0.25		K/W
P_{tot}	*total power dissipation*		T_C = 25°C			100	W
I_{FSM}	*max. forward surge current*	t = 10 ms; (50 Hz), sine	T_{VJ} = 45°C			120	A
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			130	A
		t = 10 ms; (50 Hz), sine	T_{VJ} = 150°C			100	A
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			110	A
I^2t	*value for fusing*	t = 10 ms; (50 Hz), sine	T_{VJ} = 45°C			72	A^2s
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			70	A^2s
		t = 10 ms; (50 Hz), sine	T_{VJ} = 150°C			50	A^2s
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			50	A^2s
C_J	*junction capacitance*	V_R = 400 V; f = 1 MHz	T_{VJ} = 25°C		4		pF

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Package TO-263 (D2Pak)			Ratings			
Symbol	**Definition**	**Conditions**	**min.**	**typ.**	**max.**	**Unit**
I_{RMS}	*RMS current*	per terminal			25	A
T_{VJ}	*virtual junction temperature*		-55		175	°C
T_{op}	*operation temperature*		-55		150	°C
T_{stg}	*storage temperature*		-55		150	°C
Weight				2		g
F_C	*mounting force with clip*		20		60	N

Product Marking

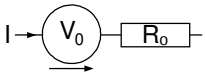


Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSP8-12AS-TRL	DSP8-12AS	Tape & Reel	800	502381
Alternative	DSP8-12AS-TUB	DSP8-12AS	Tube	50	465453

Similar Part	Package	Voltage class
DSP8-12S	TO-263AB (D2Pak) (2)	1200
DSP8-12A	TO-220AB (3)	1200
DSP8-12AC	ISOPLUS220AB (3)	1200
DSP8-08AS	TO-263AA (D2Pak) (3)	800
DSP8-08S	TO-263AB (D2Pak) (2)	800
DSP8-08A	TO-220AB (3)	800

Equivalent Circuits for Simulation

** on die level* T_{VJ} = 175 °C

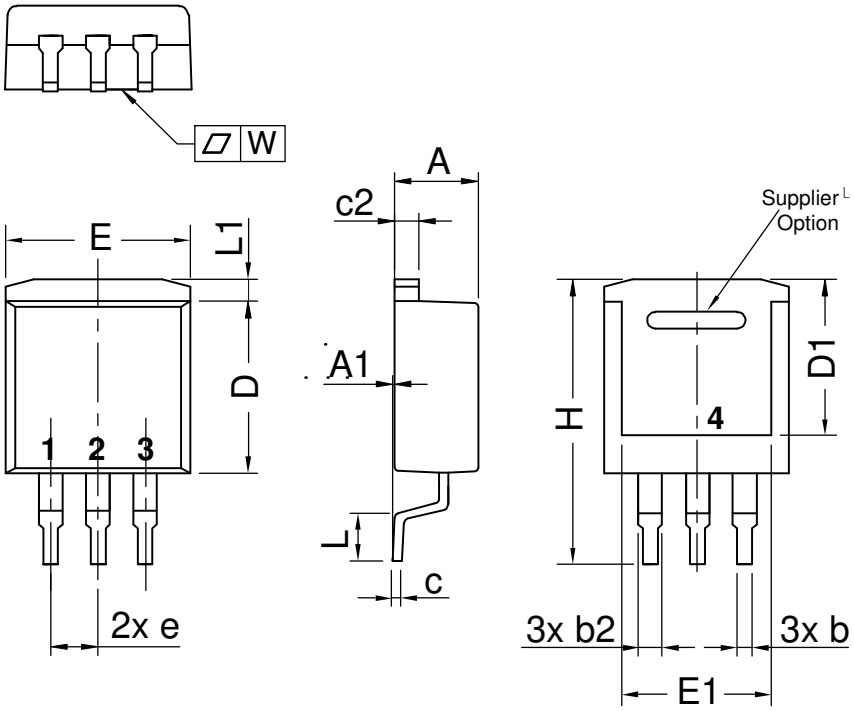


Rectifier

$V_{0\,max}$	*threshold voltage*	0.79	V
$R_{0\,max}$	*slope resistance **	30	mΩ

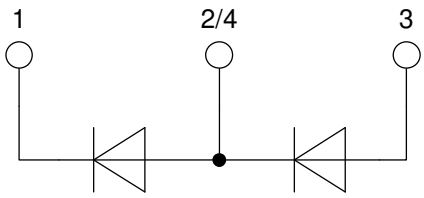
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Outlines TO-263 (D2Pak)



Dim.	Millimeter		Inches	
	min	max	min	max
A	4.06	4.83	0.160	0.190
A1	typ. 0.10		typ. 0.004	
A2	2.41		0.095	
b	0.51	0.99	0.020	0.039
b2	1.14	1.40	0.045	0.055
c	0.40	0.74	0.016	0.029
c2	1.14	1.40	0.045	0.055
D	8.38	9.40	0.330	0.370
D1	8.00	8.89	0.315	0.350
D2	2.5		0.098	
E	9.65	10.41	0.380	0.410
E1	6.22	8.50	0.245	0.335
e	2,54 BSC		0,100 BSC	
e1	4.28		0.169	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	1.02	1.68	0.040	0.066
W	typ. 0.02	0.040	typ. 0.0008	0.002

All dimensions conform with and/or within JEDEC standard.



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Rectifier

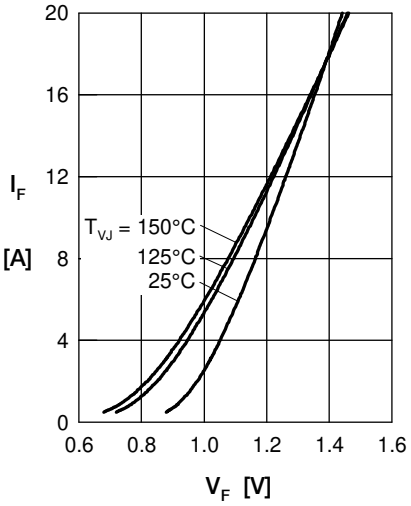


Fig. 1 Forward current versus voltage drop per diode

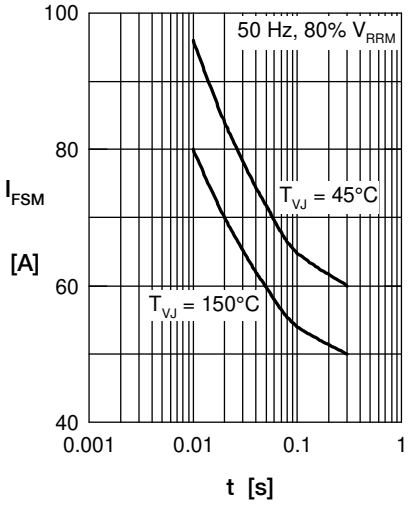


Fig. 2 Surge overload current

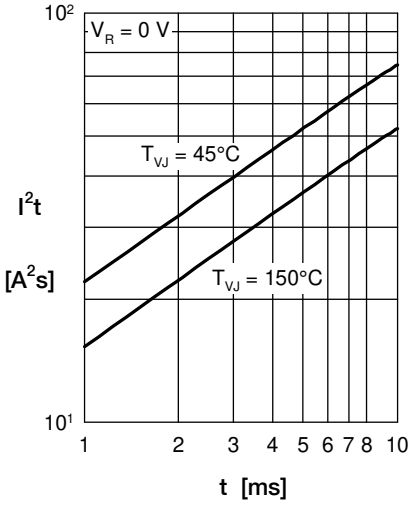


Fig. 3 I^2t versus time per diode

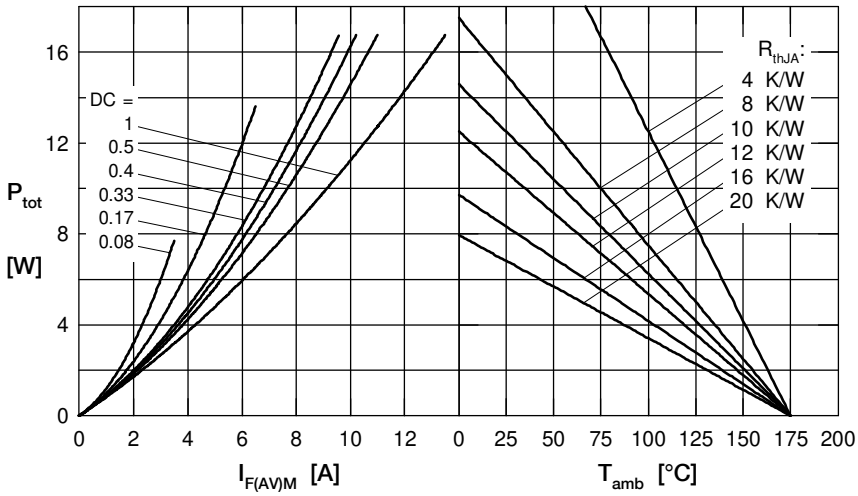


Fig. 4 Power dissipation vs. direct output current and ambient temperature

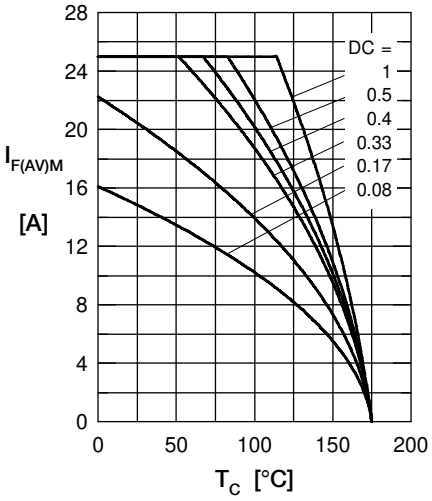


Fig. 5 Max. forward current vs. case temperature

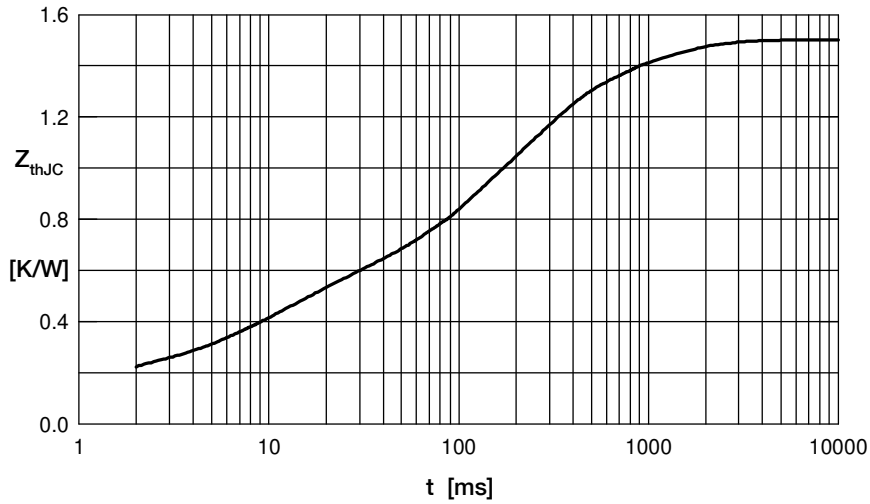


Fig. 6 Transient thermal impedance junction to case

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.155	0.0005
2	0.332	0.0095
3	0.713	0.17
4	0.3	0.8
5	0.00001	0.00001

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